

T510X157K016ATE030

T510, Tantalum, MnO₂ Tantalum, Multi-Anode, 150 uF, 10%, 16 VDC, SMD, MnO₂, Molded, Multiple Anodes, Low ESR, 30 mOhms, 7343, 4.3mm



Click [here](#) for the 3D model.

Dimensions

Footprint	7343
L	7.3mm +/-0.3mm
W	4.3mm +/-0.3mm
H	4mm +/-0.3mm
T	0.13mm REF
S	1.3mm +/-0.3mm
F	2.4mm +/-0.1mm
A	3.8mm MIN
B	0.5mm +/-0.15mm
E	3.5mm REF
G	3.5mm REF
P	1.7mm REF
R	1mm REF
X	0.1mm +/-0.1mm REF

Packaging Specifications

Packaging	T&R, 178mm
Packaging Quantity	500

General Information

Series	T510
Dielectric	MnO ₂ Tantalum
Style	SMD Chip
Description	SMD, MnO ₂ , Molded, Multiple Anodes, Low ESR
Features	Low ESR
RoHS	Yes
Termination	Tin
AEC-Q200	No
Typical Component Weight	430.15 mg
Shelf Life	156 Weeks
MSL	1

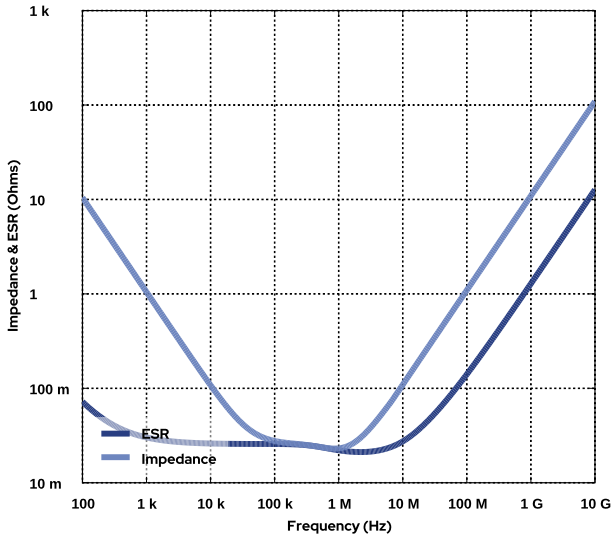
Specifications

Capacitance	150 uF
Capacitance Tolerance	10%
Voltage DC	16 VDC (85C), 10.72 VDC (125C)
Temperature Range	-55/+125°C
Rated Temperature	85°C
Dissipation Factor	6% 120Hz 25C
Failure Rate	N/A
ESR	30 mOhms (100kHz 25C)
Ripple Current	3000 mA (rms, 100kHz 25C), 2700 mA (rms, 85C), 1200 mA (rms, 125C)
Leakage Current	24 uA (5min 25°C)

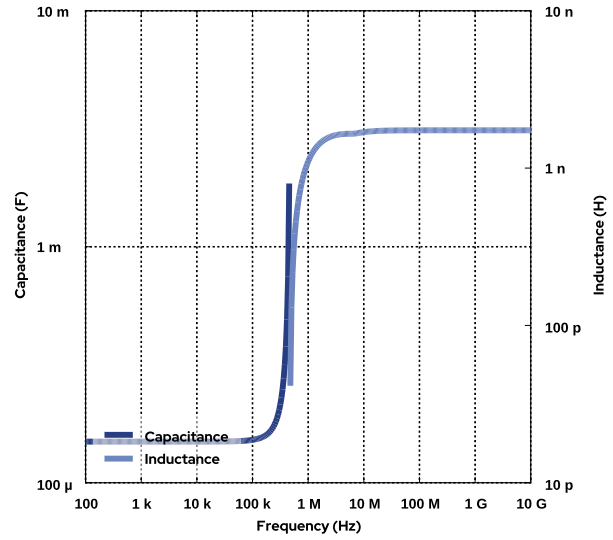
Simulations

For the complete simulation environment please visit [K-SIM](#).

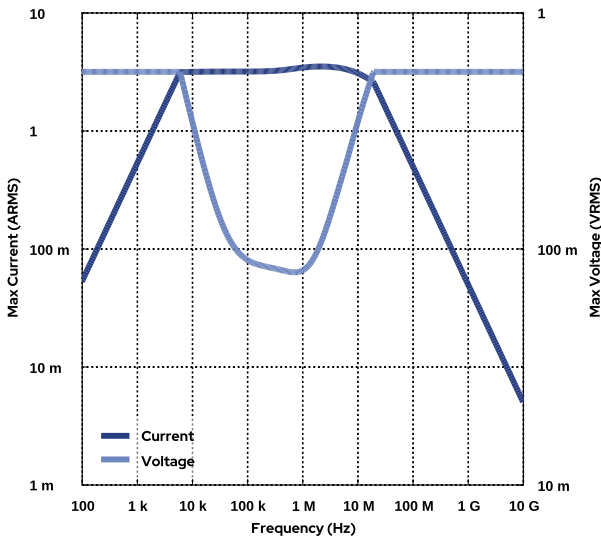
Impedance and ESR



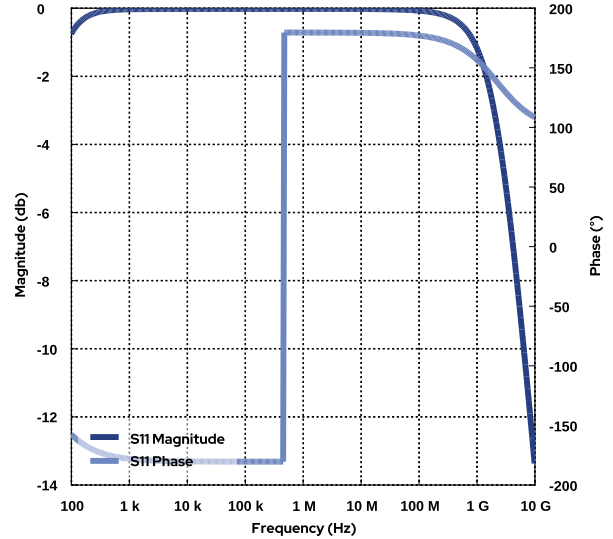
Capacitance and Inductance

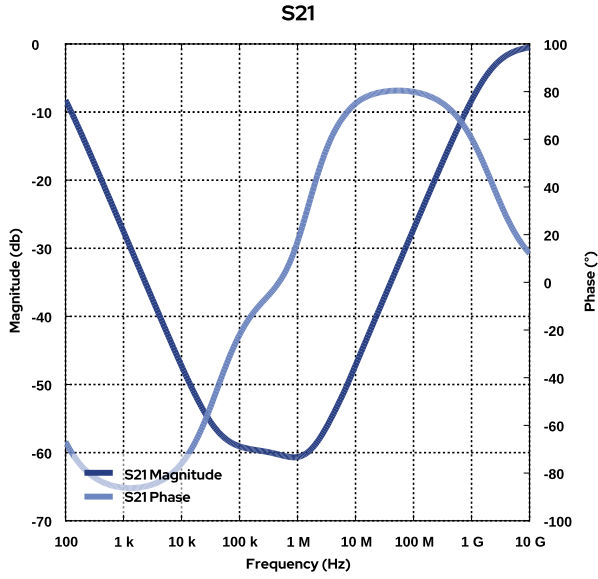


Current and Voltage



S11





These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.
- The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
- The effects shown herein are based on measured data from a multiple part sample of the parts in question.
- Ripple capability of this device will be factored by thermal resistance (R_{th}) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.
- The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages generated at any other harmonics.
- Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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If you have any questions please contact K-SIM.